Topological insulators and superconductors

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1. Chern insulator and IQHE

- Integer quantum Hall effect
- Chern insulator on square lattice
- Topological invariant



The Integer Quantum Hall State

Integer Quantum Hall State:

First example of 2D topological material



[von Klitzing '80]

The Integer Quantum Hall State

What causes the precise quantization in IQHE?

Explanation One: Edge state transport

IQHE has an energy gap in the bulk:



- charge cannot flow in bulk; only along 1D channels at edges (chiral edge states) $\frac{-\sigma}{2}$
- chiral edge state cannot be localized by disorder (no backscattering)
- edge states are perfect charge conductor!

Explanation Two: Topological band theory

Distinction between the integer quantum Hall state and a conventional insulator $H = -iv(\sigma_{a} + \sigma_{b}) + m(v)\sigma_{z}$ is a topological property of the band structure **[Thouless et al, 84]**

$$\begin{array}{ccc} \mathcal{H}(\mathbf{k}) : & \text{Brillouin zone} & & & \text{Hamiltonians with energy gap} \\ \text{Classified by Chern number:} & n = \frac{i}{2\pi} \sum_{\substack{\text{filled} \\ \text{states}}} \int \mathcal{F} d^2 k & (= \text{topological invariant}) & n \in \mathbb{Z} \\ \\ \hline & \text{Kubo formula:} & \sigma_{xy} = \frac{e^2}{h} \frac{i}{2\pi} \sum_{\substack{\text{filled} \\ \text{states}}} \int \mathcal{F} d^2 k \end{array}$$

does not change under smooth deformations, as long as bulk energy gap is not closed

Bulk-boundary correspondence

topological invariant

$$n = \frac{i}{2\pi} \sum_{\substack{\text{filled}\\\text{states}}} \int \mathcal{F} d^2 k$$

 $n \in \mathbb{Z}$

Zero-energy state at interface



Bulk-boundary correspondence:

Zero-energy states must exist at the interface between two different topological phases

Follows from the quantization of the topological invariant.

 $\Delta n = |n_{
m L} - n_{
m R}|\;$ = number or edge modes

Stable gapless edge states:

- robust to smooth deformations (respect symmetries of the system)
- insensitive to disorder, impossible to localize
- cannot exist in a purely 1D system (Fermion doubling theorem)

IQHE: chiral Dirac Fermion





Chern insulator ("integer quantum Hall state on a lattice")



Chern insulator on square lattice

Chern insulator on square lattice: $\mathcal{H}_{CI} = \mathbf{d}(\mathbf{k}) \cdot \vec{\sigma} + \epsilon_0(\mathbf{k})\sigma_0$

 $d_x(\mathbf{k}) = \sin k_x \qquad d_y(\mathbf{k}) = \sin k_y \qquad d_z(\mathbf{k}) = (2 + M - \cos k_x - \cos k_y)$

Effective low-energy continuum theory for M=0: (expand around $\mathbf{k} = 0$; σ_0 term can be neglected)

$$H_{\rm CI} = k_x \sigma_x + k_y \sigma_y + M \sigma_z$$

two eigenfunctions with energies: $E_{\pm} = \pm \lambda = \pm \sqrt{\mathbf{k}^2 + M^2}$

$$\left|u_{\mathbf{k}}^{+}\right\rangle = \frac{1}{\sqrt{2\lambda(\lambda - M)}} \begin{pmatrix}k_{x} - ik_{y}\\\lambda - M\end{pmatrix} \qquad \left|u_{\mathbf{k}}^{-}\right\rangle = \frac{1}{\sqrt{2\lambda(\lambda + M)}} \begin{pmatrix}-k_{x} + ik_{y}\\\lambda + M\end{pmatrix}$$

Berry curvature: $F_{xy} = \partial_{k_x} A_{k_y} - \partial_{k_y} A_{k_x} = + \frac{1}{2\lambda^3}$ gives

zero-energy state at boundary

gives nonzero Chern number
$$n = \frac{1}{2\pi} \int d^2k F_{xy} = \frac{1}{2} \operatorname{sgn}(M)$$
 (= Hall conductance σ_{xy})

NB: Chern number must be integer for integrals over compact manifolds. Proper regularization of Dirac Hamiltonian will lead to $n \in \mathbb{Z}$

 $\psi_0 = \frac{1}{\sqrt{2}} \begin{pmatrix} 1\\ -1 \end{pmatrix} e^{ik_y y} e^{-\int_0^x M(x') dx'}$ Chiral edge state at boundary between two Chern insulators with different n

$$n = 0 \qquad n = 1$$

Experimental realisation of Chern insulator

Cr-doped (Bi,Sb)₂Te₃

 Thin layer of topological insulator, which has helical surface states

 States on top surface are gapped out by finite size quantization

Time-reversal symmetry is broken by magnetic ad-atoms (Cr or V)





Fig. 3. The QAH effect under strong magnetic field measured at 30 mK. (A) Magnetic field dependence of ρ_{yx} at V_g^0 . (B) Magnetic field dependence of ρ_{xx} at V_g^0 . The blue and red lines in (A) and (B) indicate the data taken with increasing and decreasing fields, respectively.

[Chang et al. Science '13]